

# Developing a simulation for estimation of SiPM optical cross talk level

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On behalf of JADDE collaboration

CAP Congress 2022

8 June 2022

# SiPMs

SiPMs are **photodetectors**.

They are arrays of APDs (semiconductor detectors), which are operating in Geiger mode outputting the sum of cell signal.

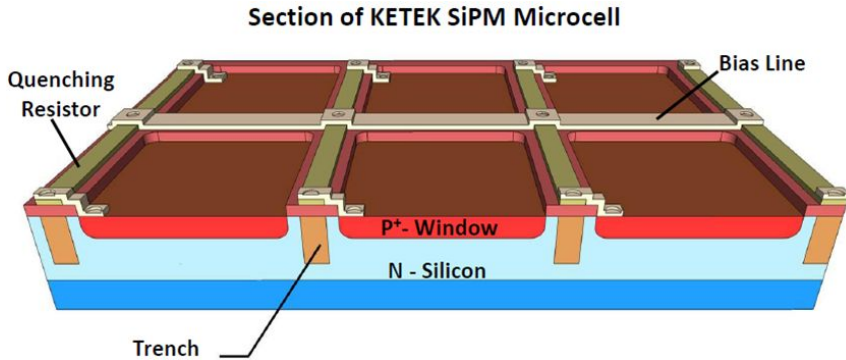


Figure: SiPM schematics

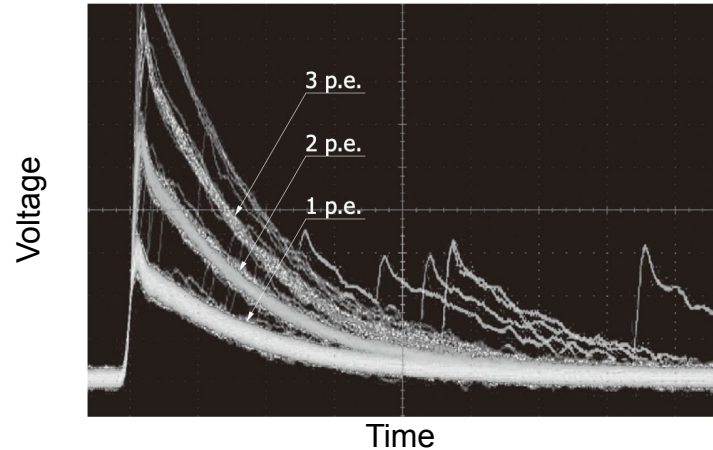


Figure: SiPM signal

# SiPMs

One photon - one photo electron (p.e.) height of the output signal.

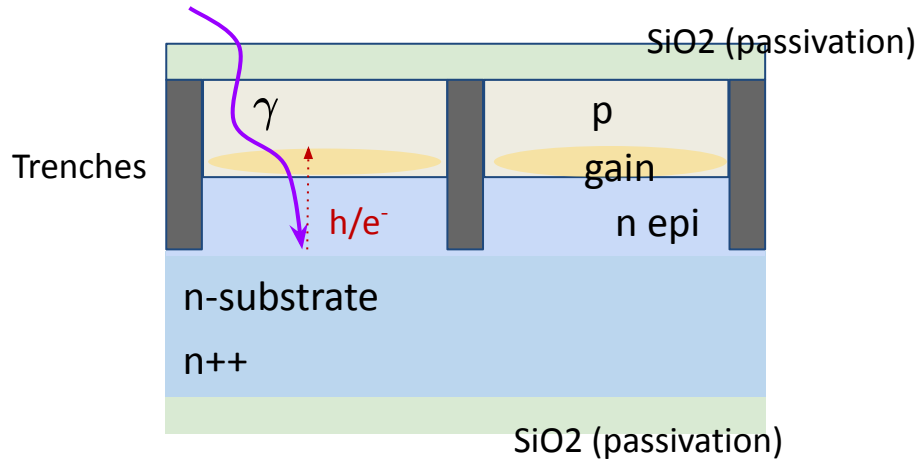


Figure: SiPM schematics

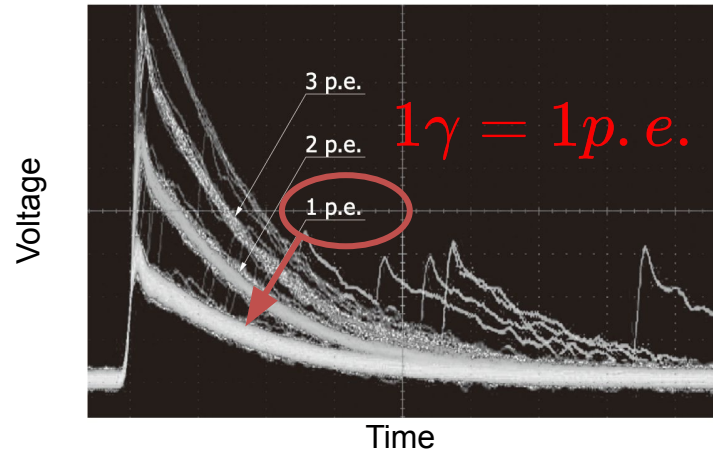


Figure: SiPM signal

# SiPMs

Two photons - two photo electron (p.e.) height of the output signal.

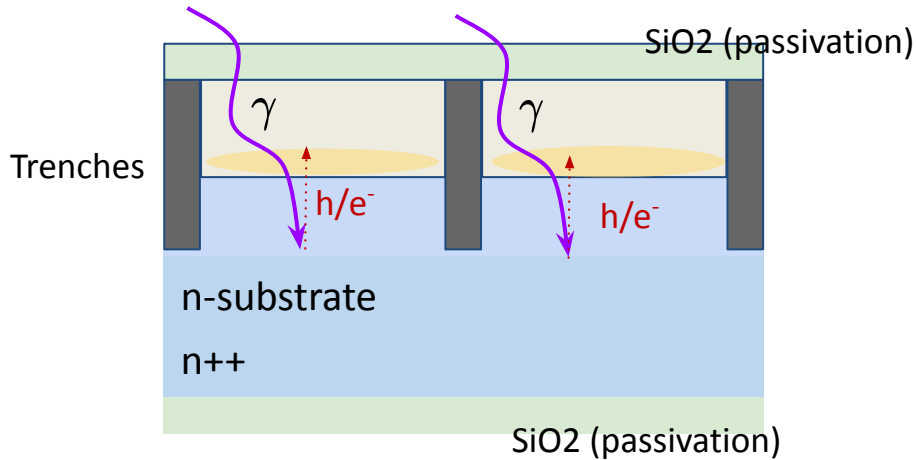


Figure: SiPM schematics

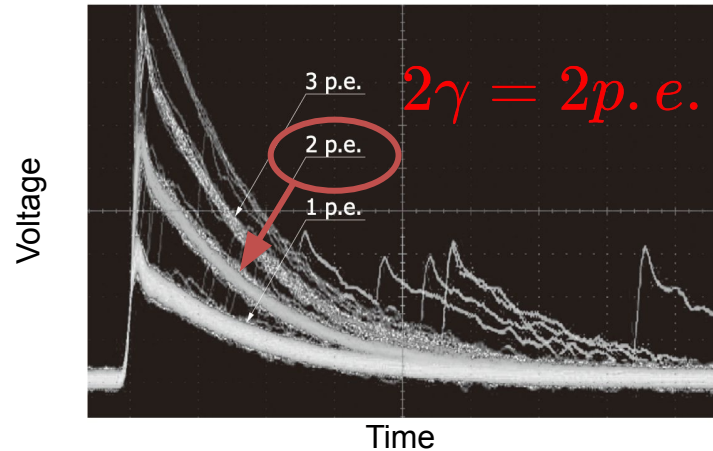


Figure: SiPM signal

# Optical crosstalk

- APD cells located close to each other ( $\sim\mu\text{m}$ )
- Photons produced in an avalanche can trigger neighbour cell.
- Create artificial increase in signal

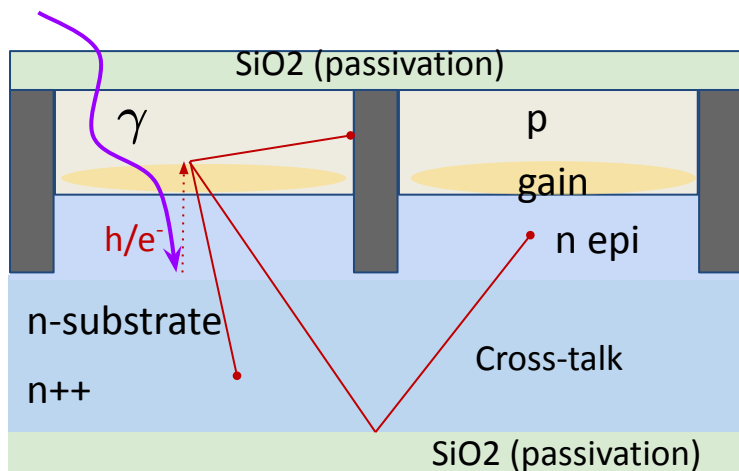


Figure: SiPM optical cross talk illustration

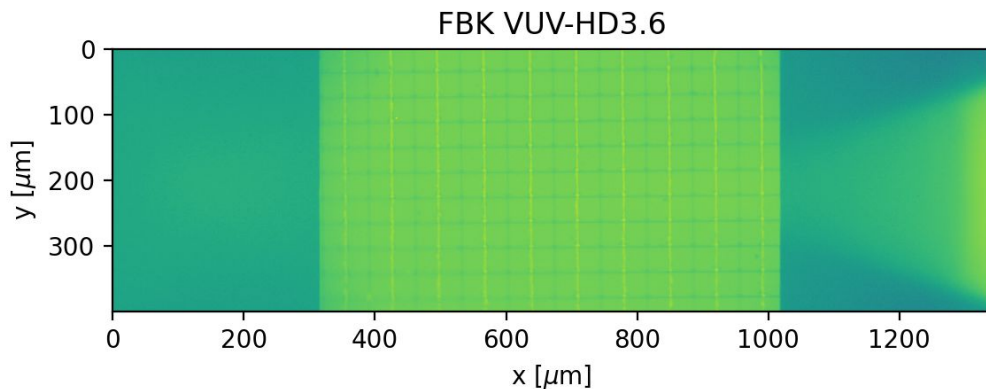


Figure: SiPM photo

# Optical crosstalk

- APD cells located close to each other ( $\sim\mu\text{m}$ )
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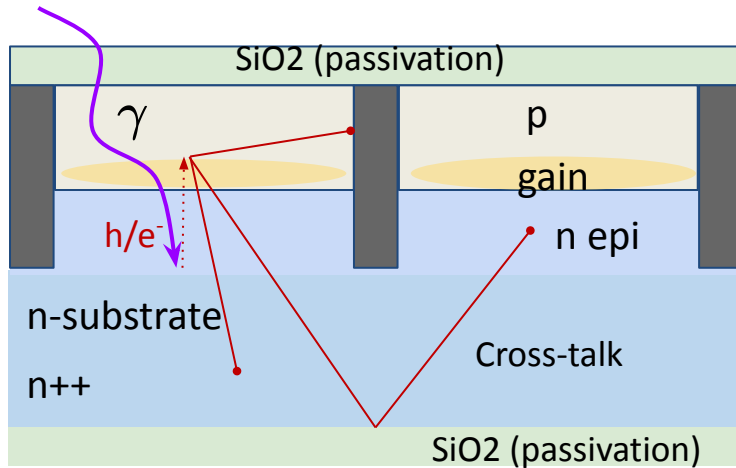


Figure: SiPM optical cross talk illustration

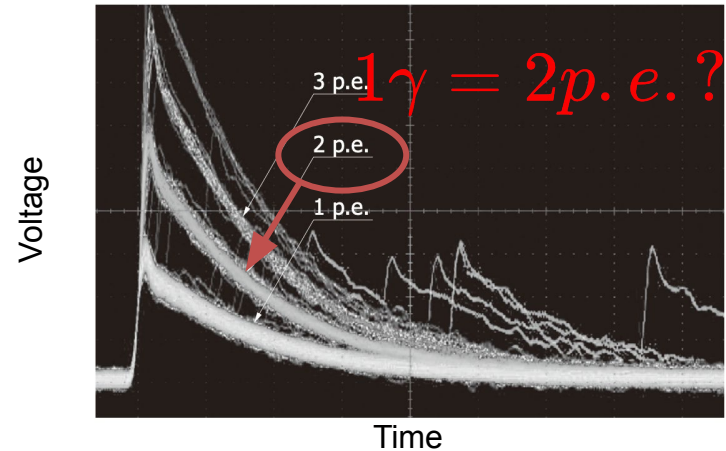


Figure: SiPM signal

# Optical crosstalk

- Undesirable and unavoidable process
- Can be measured but requires a detector prototype, which is expensive to produce
- We would like to predict and minimize it in advance

# Optical crosstalk

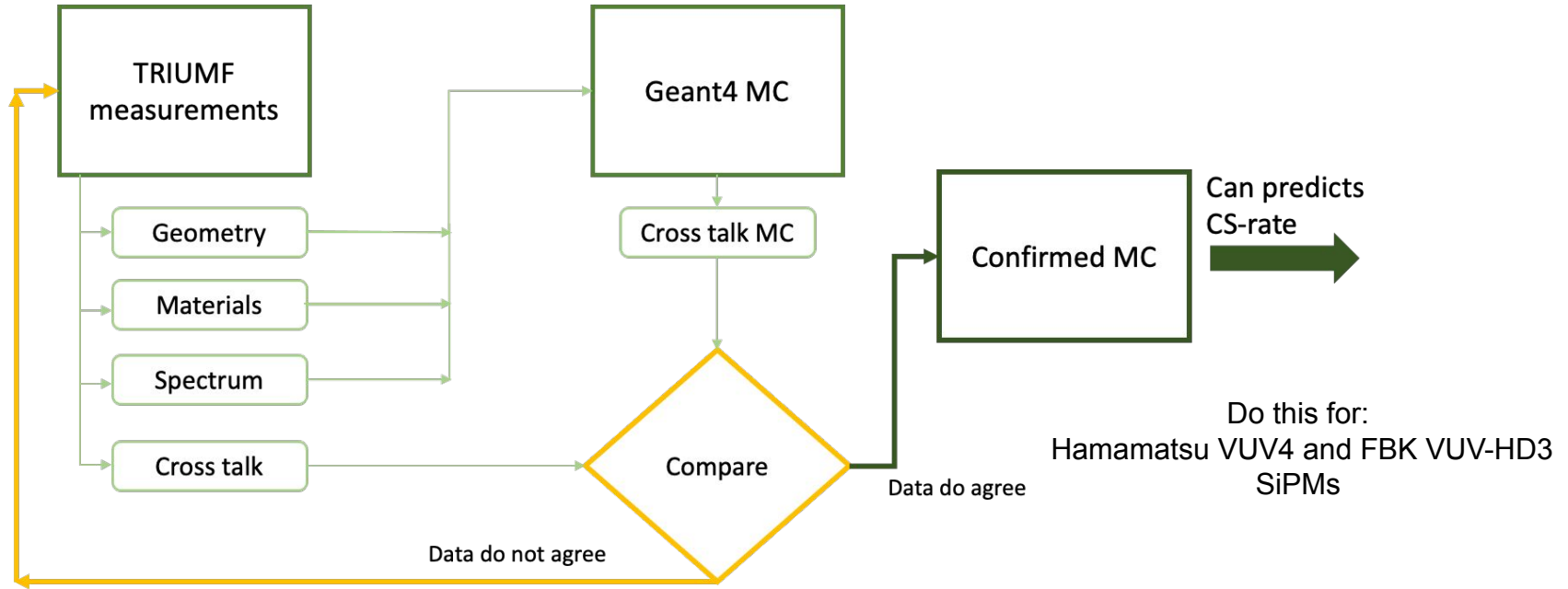
- Undesirable and unavoidable process
- Can be measured but requires a detector prototype, which is expensive to produce
- We would like to predict and minimize it in advance



**Create a simulation**

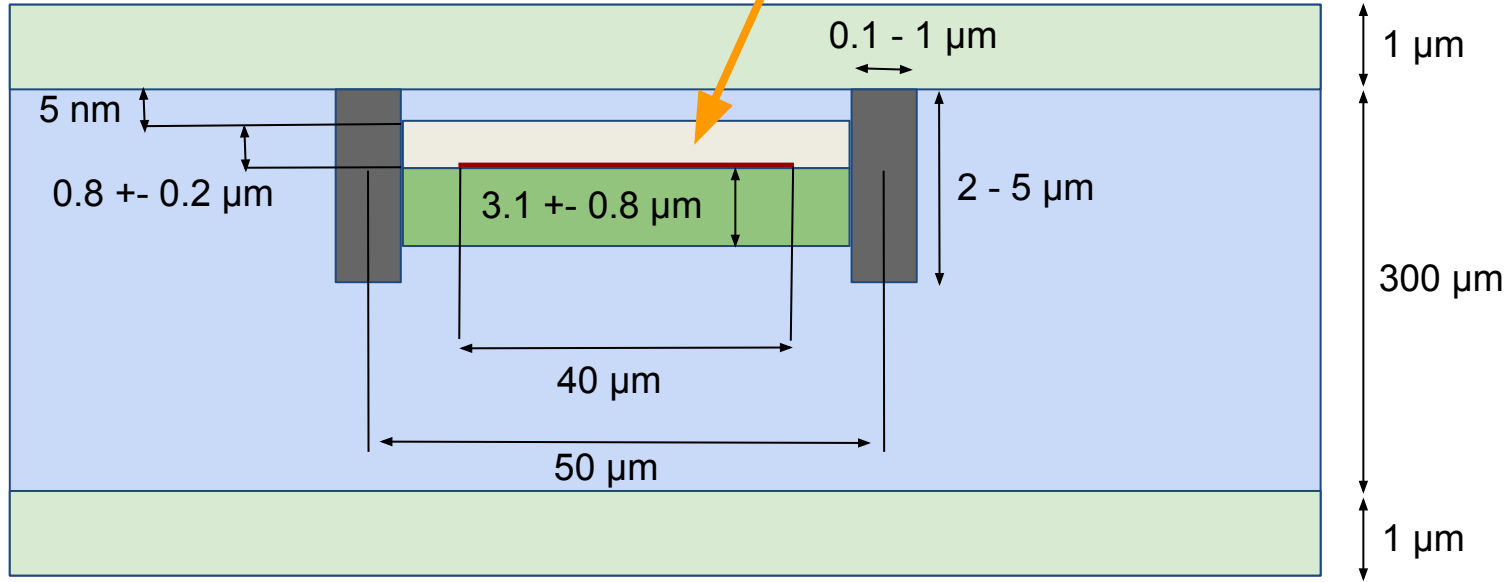








# SiPM crosstalk simulation



# Geometry example (Hamamatsu VUV4)

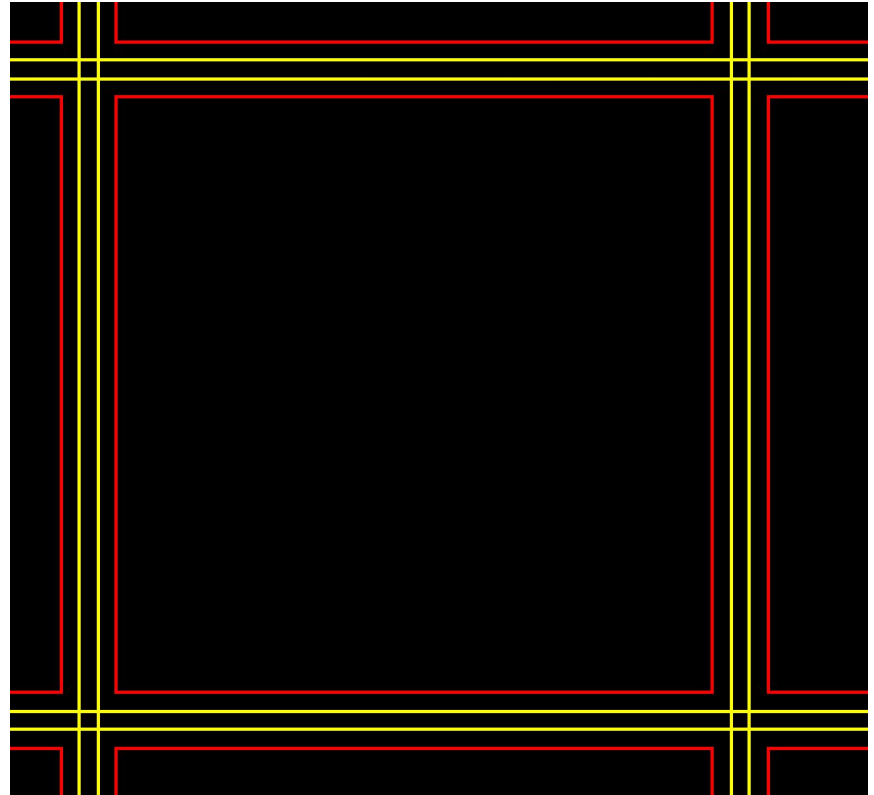
Generate secondary photons here



-  - Initial photons position
-  - SiO<sub>2</sub> layer
-  - Silicon
-  - Trenches
-  - Electron generating region
-  - Holes generating region

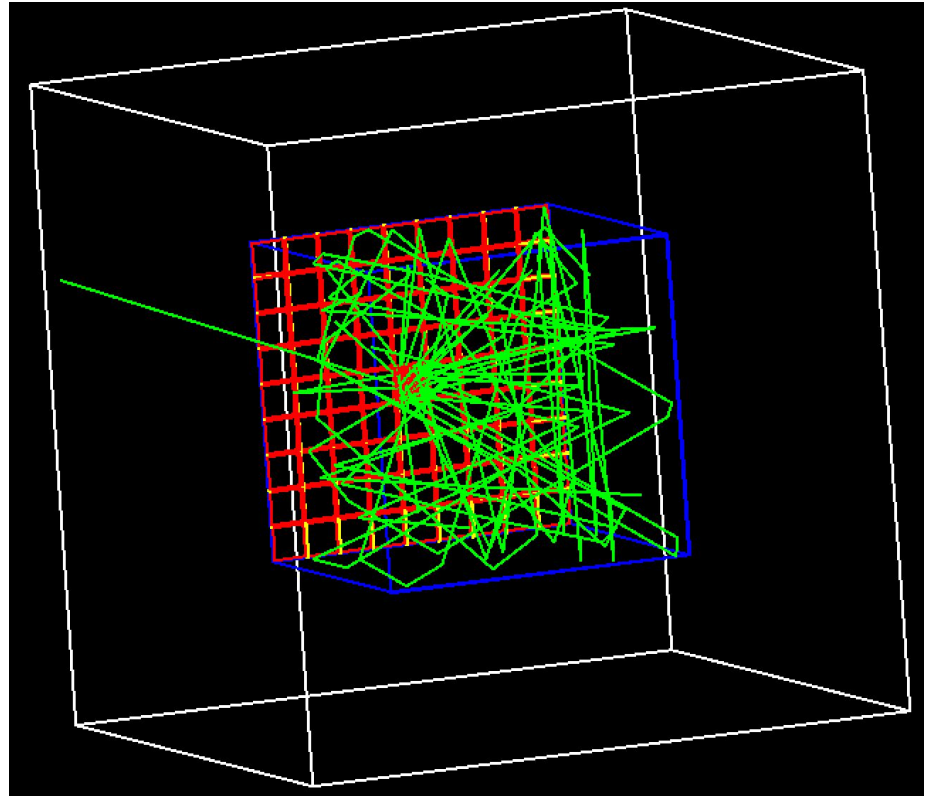
# Geant4 geometry

Here you can see the top view of the cells. The trenches are yellow lines, the avalanche area is in red.



# Geant4 geometry

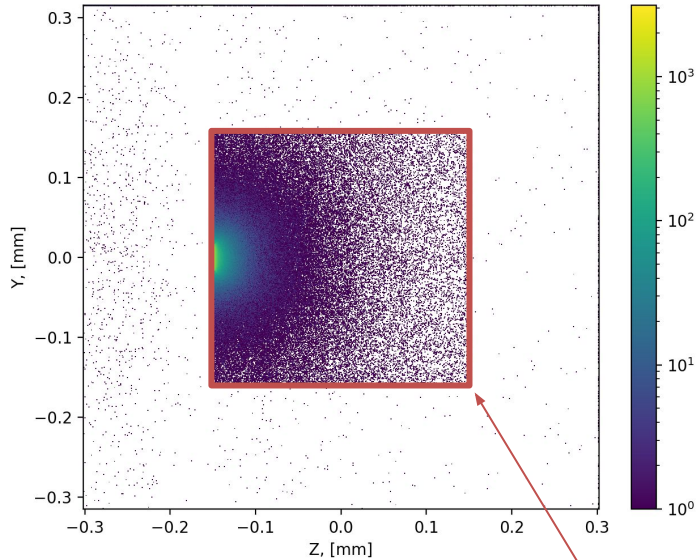
- Photons with wavelength from 440 nm to 1000 nm are produced in the avalanche region.
- Final positions and properties of the photons are stored



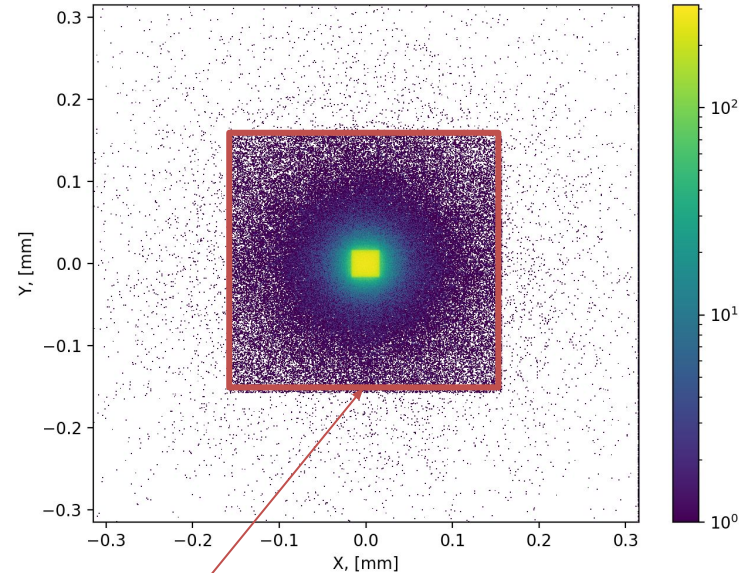
# Analysis

Final positions of all secondary photons

## FBK YZ plane

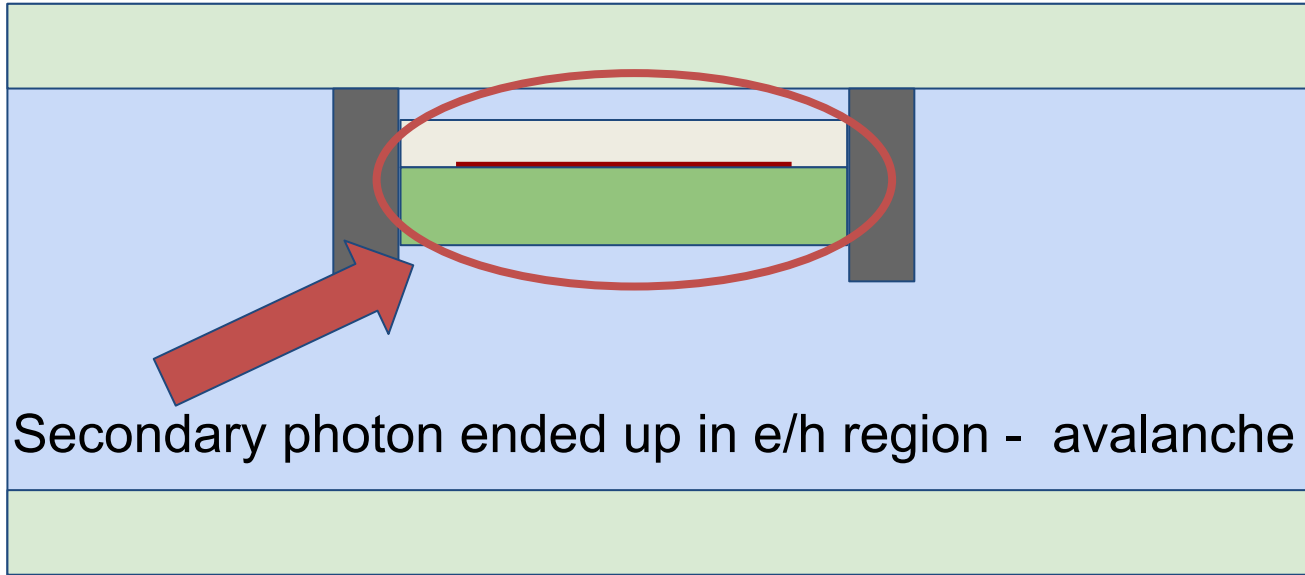


## FBK XY plane



SiPM volume boundaries

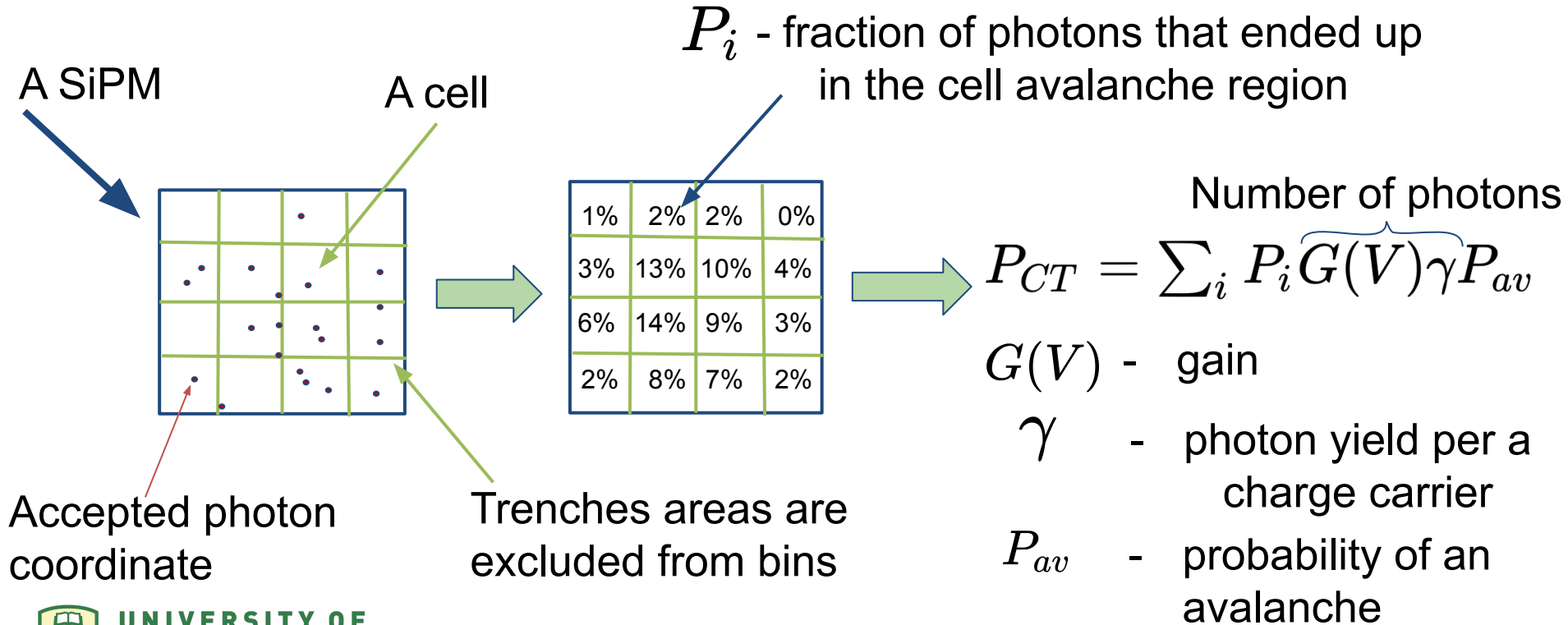
# What we count as a secondary avalanche



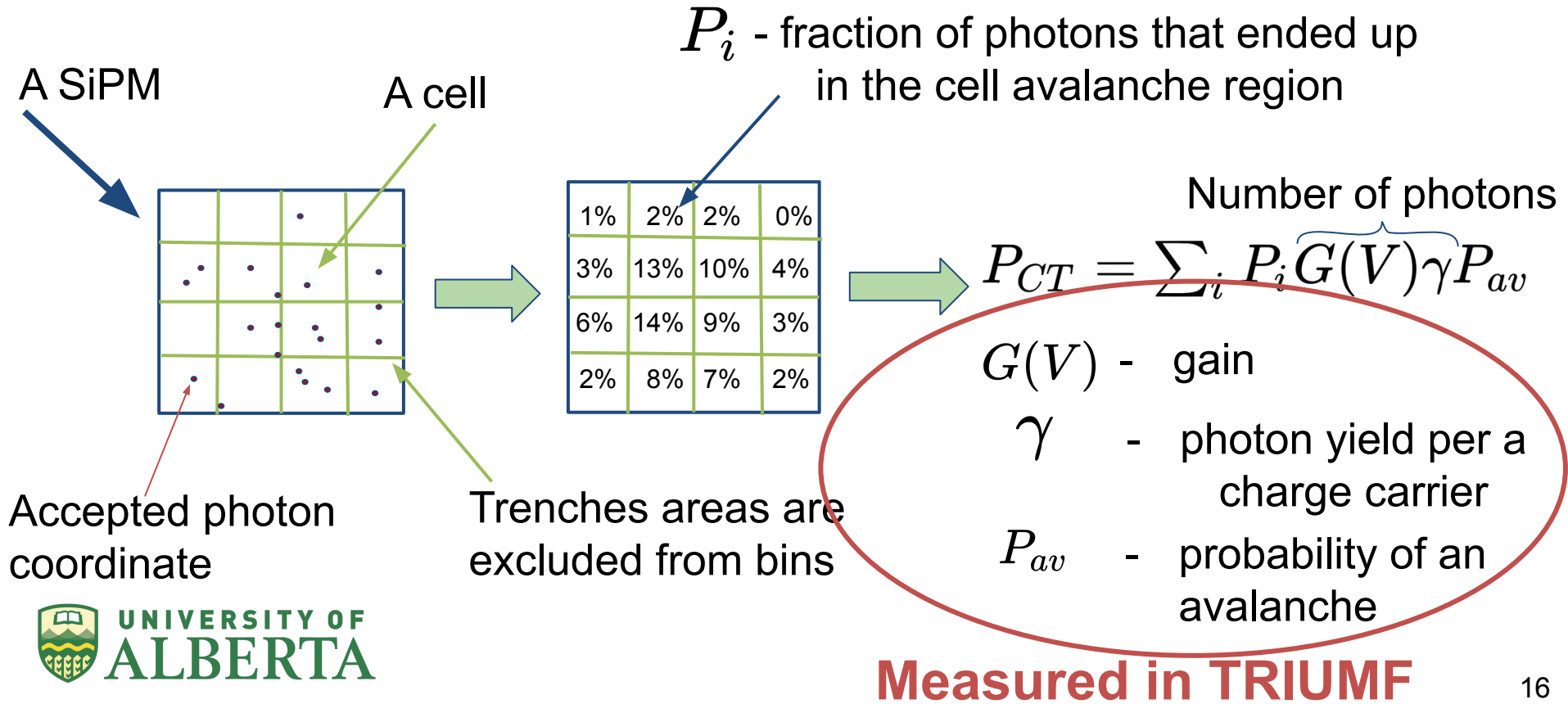
Secondary photon ended up in e/h region - avalanche

- Initial photons position
- SiO<sub>2</sub> layer
- Silicon
- Trenches
- Electron generating region
- Holes generating region

# Analysis



# Analysis





# Crosstalk MC vs Measured

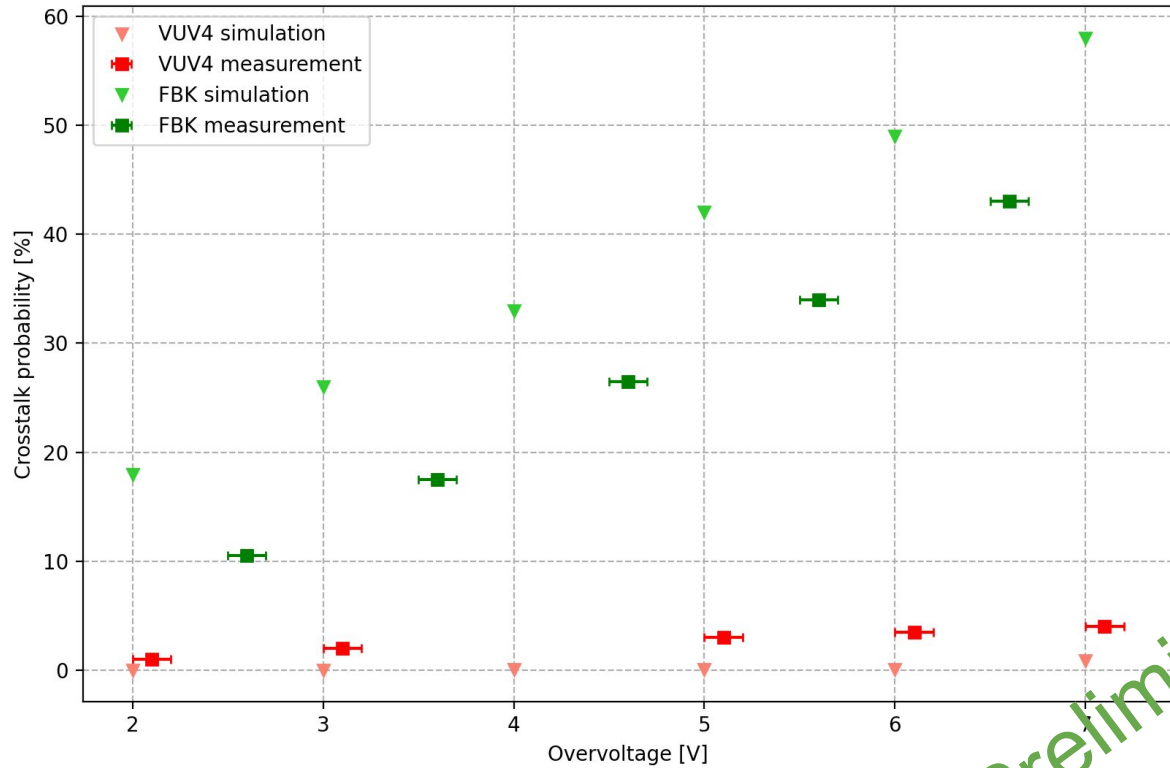
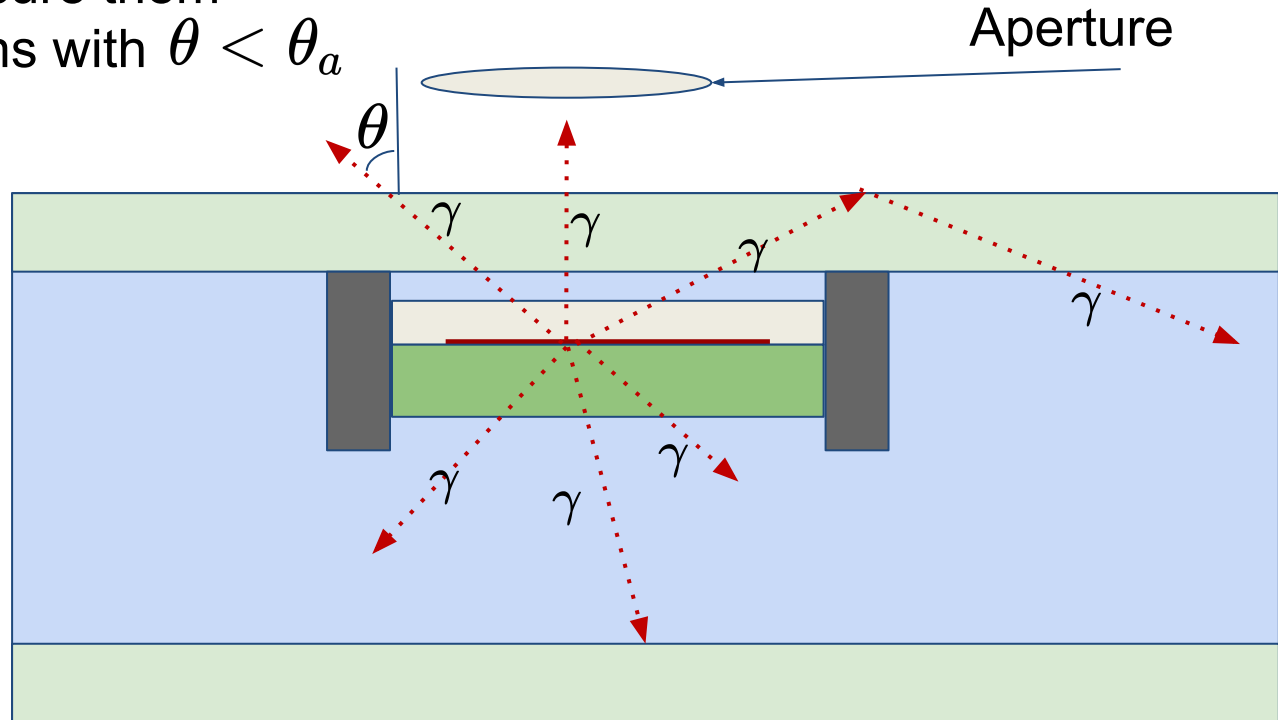


Figure: Optical crosstalk levels for different voltages

Preliminary

# Emitted light

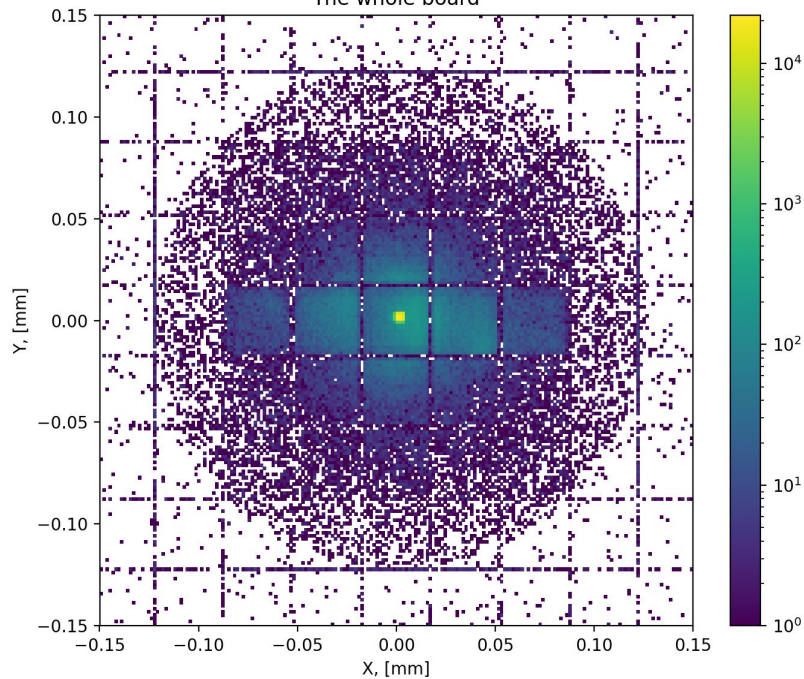
- Some of the secondary photons escape the SiPM
- We can measure them
- Select photons with  $\theta < \theta_a$



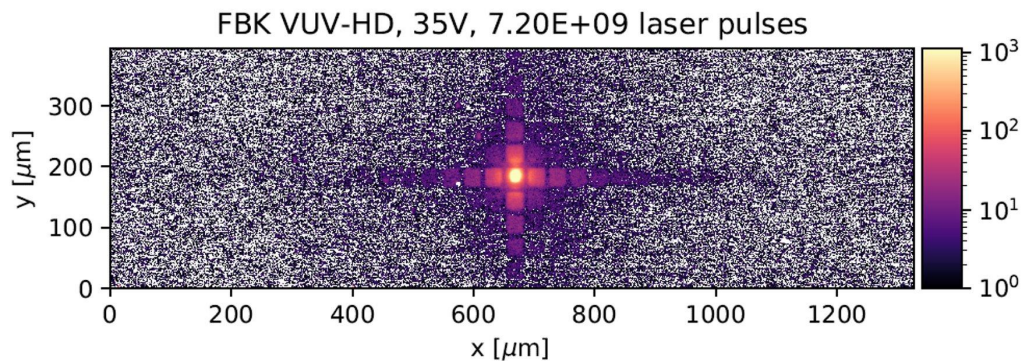
# Emitted light FBK (poly-si trenches)

Simulated

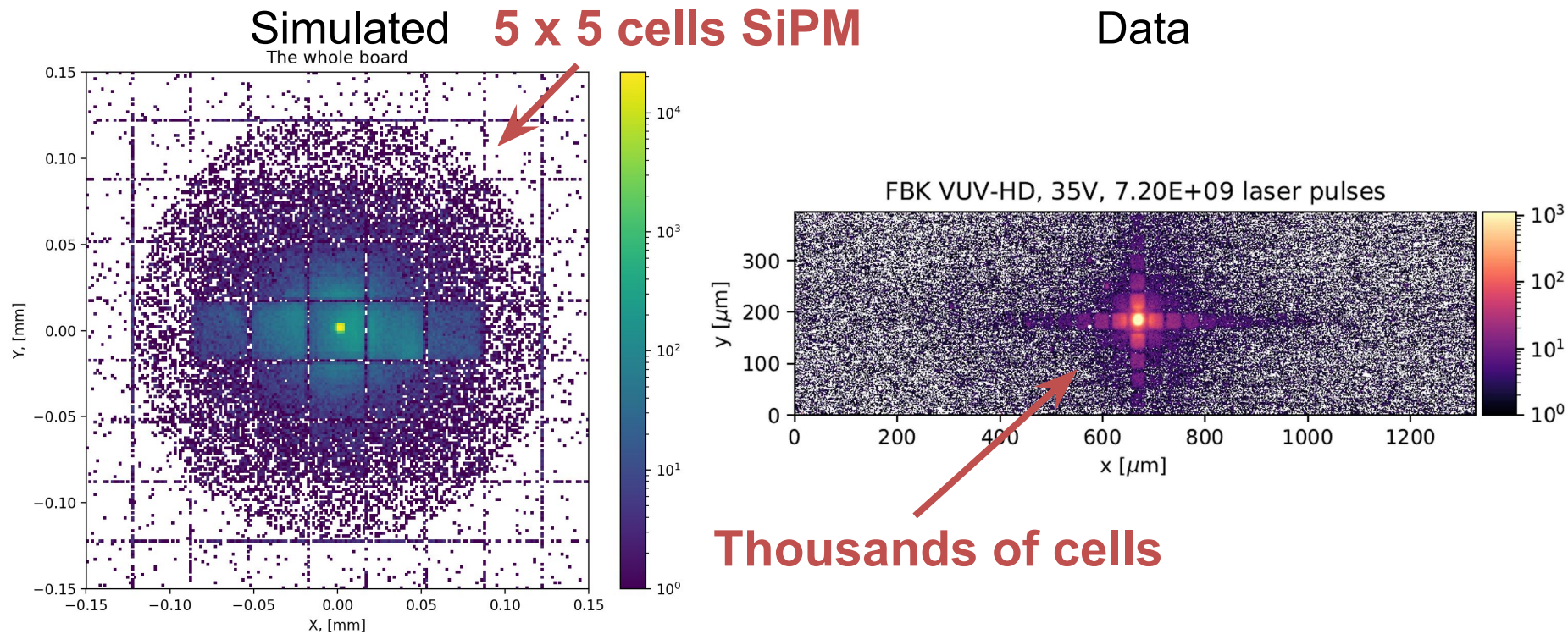
The whole board



Data



# Emitted light FBK (poly-si trenches)



# Conclusion and ongoing work

- We developed a MC simulation of optical cross talk
- We have preliminary results that give good qualitative agreement with the data
- Make the code work in parallel and get more quantitative data
- Fit data and MC
- Eventually will be able to predict cross talk levels of new possible designs of SiPMs including back side illuminated SiPMs

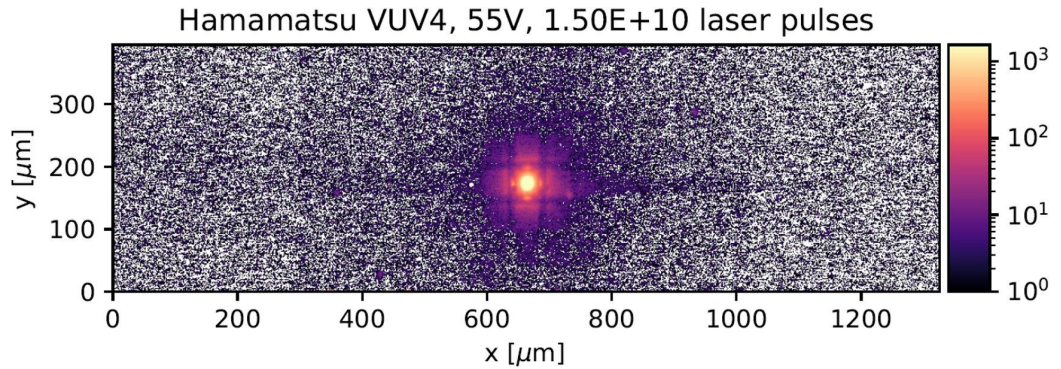
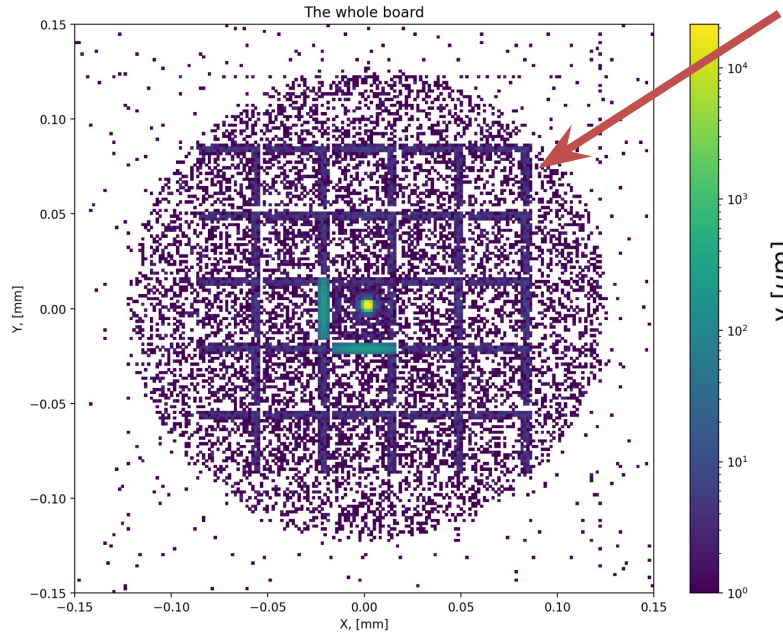
**Thank you for your attention!**

# Back Up

# Emitted light Hamamatsu (Tungsten trenches)

Simulated

Weird artifacts when we change trenches material to tungsten

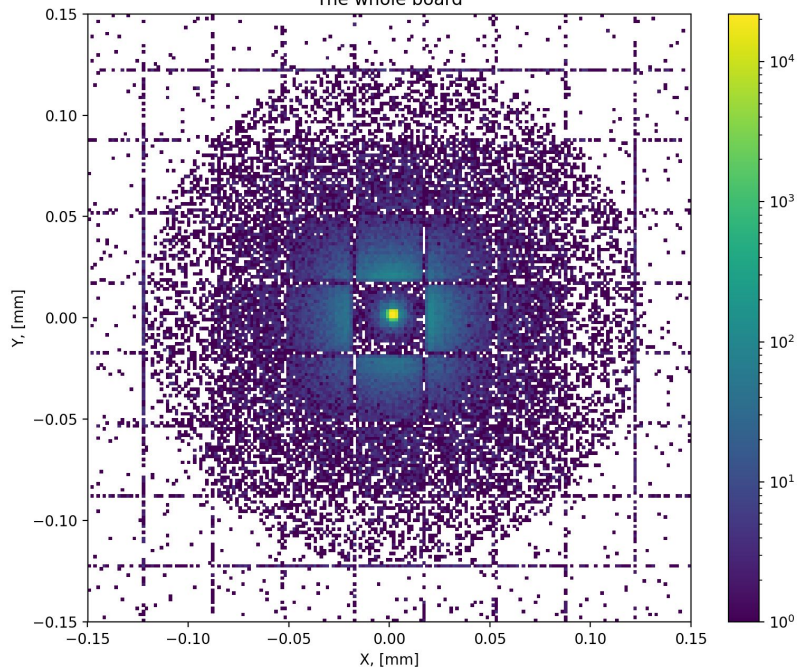




# Emitted light FBK (poly-si trenches)

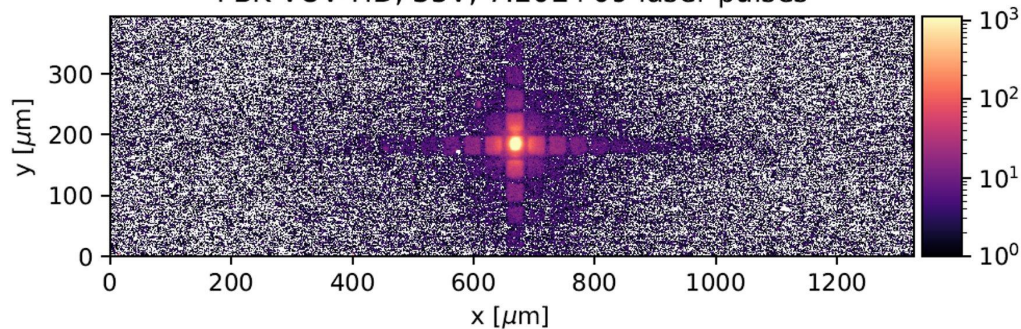
## Simulated

The whole board



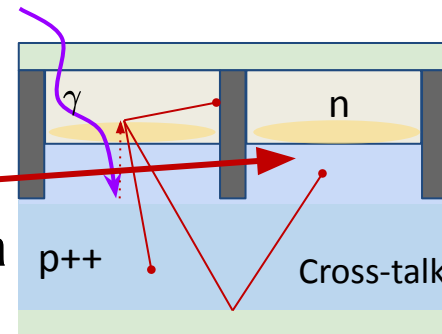
## Data

FBK VUV-HD, 35V,  $7.20E+09$  laser pulses

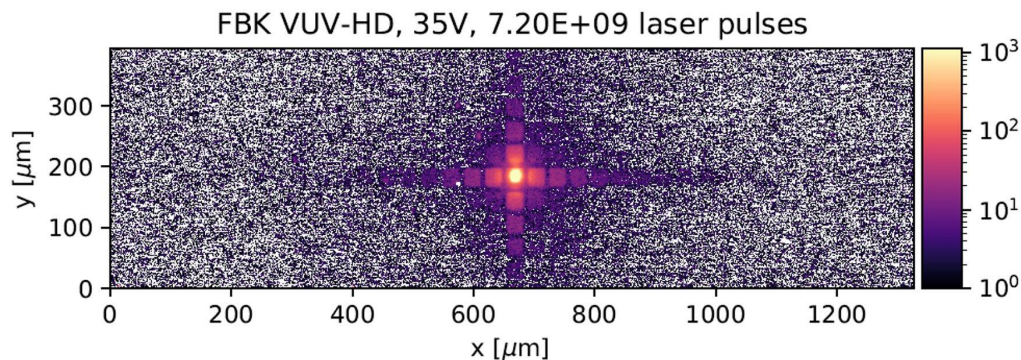
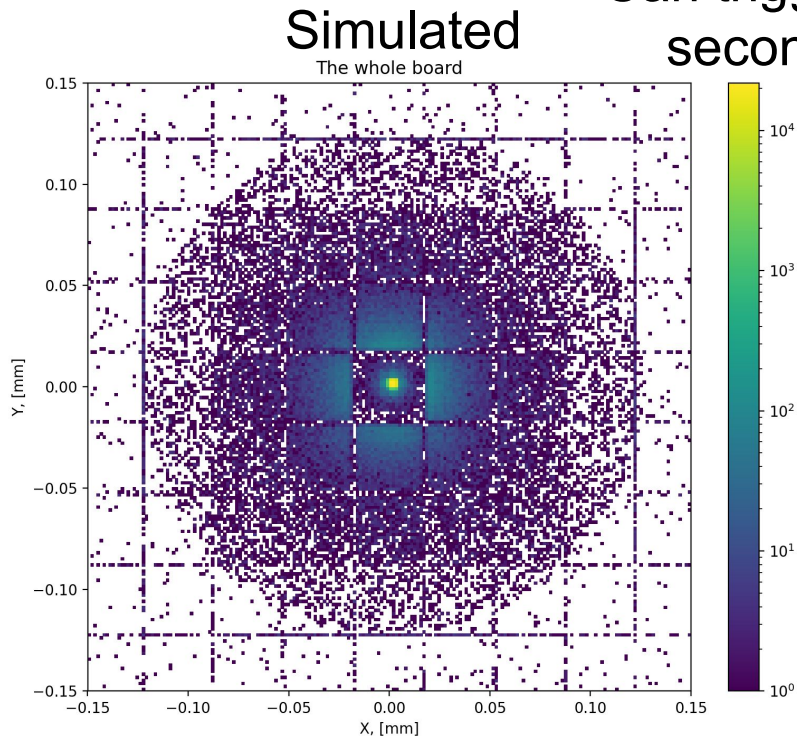


# Emitted light FBK (poly-si trenches)

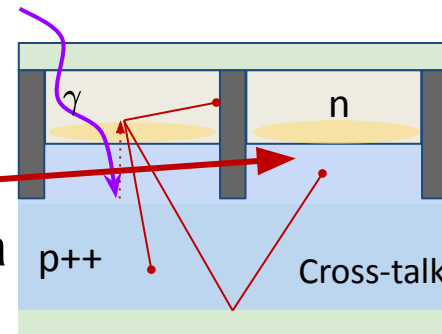
Can trigger another secondary CT



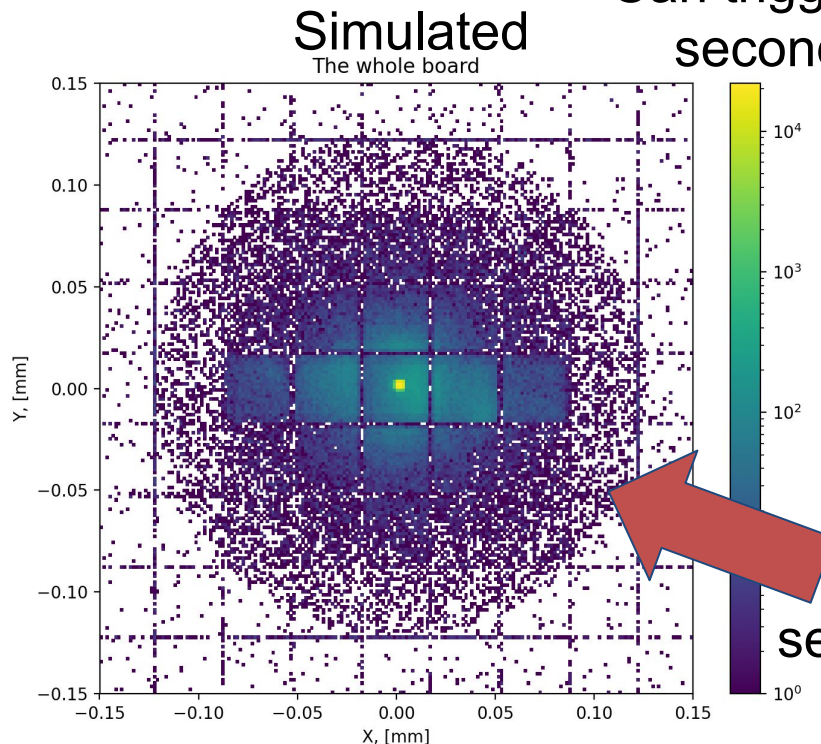
Data



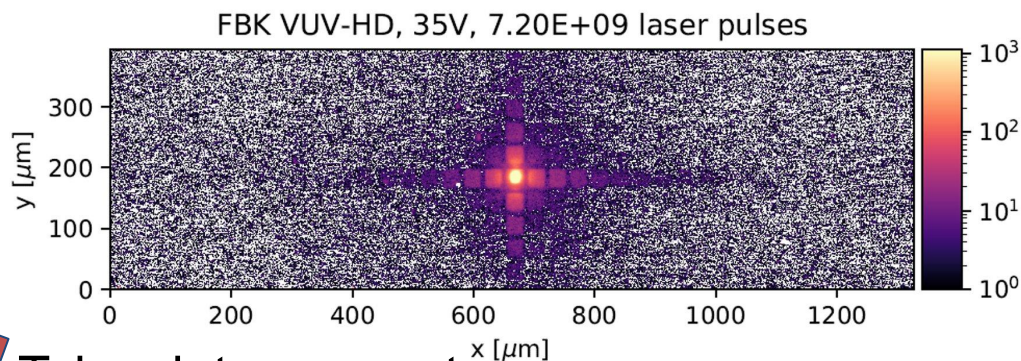
# Emitted light FBK (poly-si trenches)



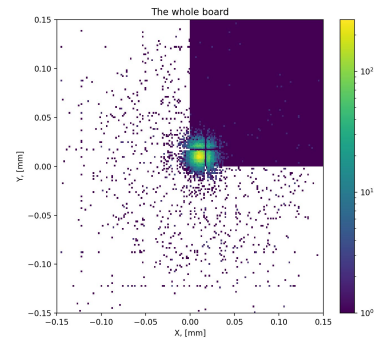
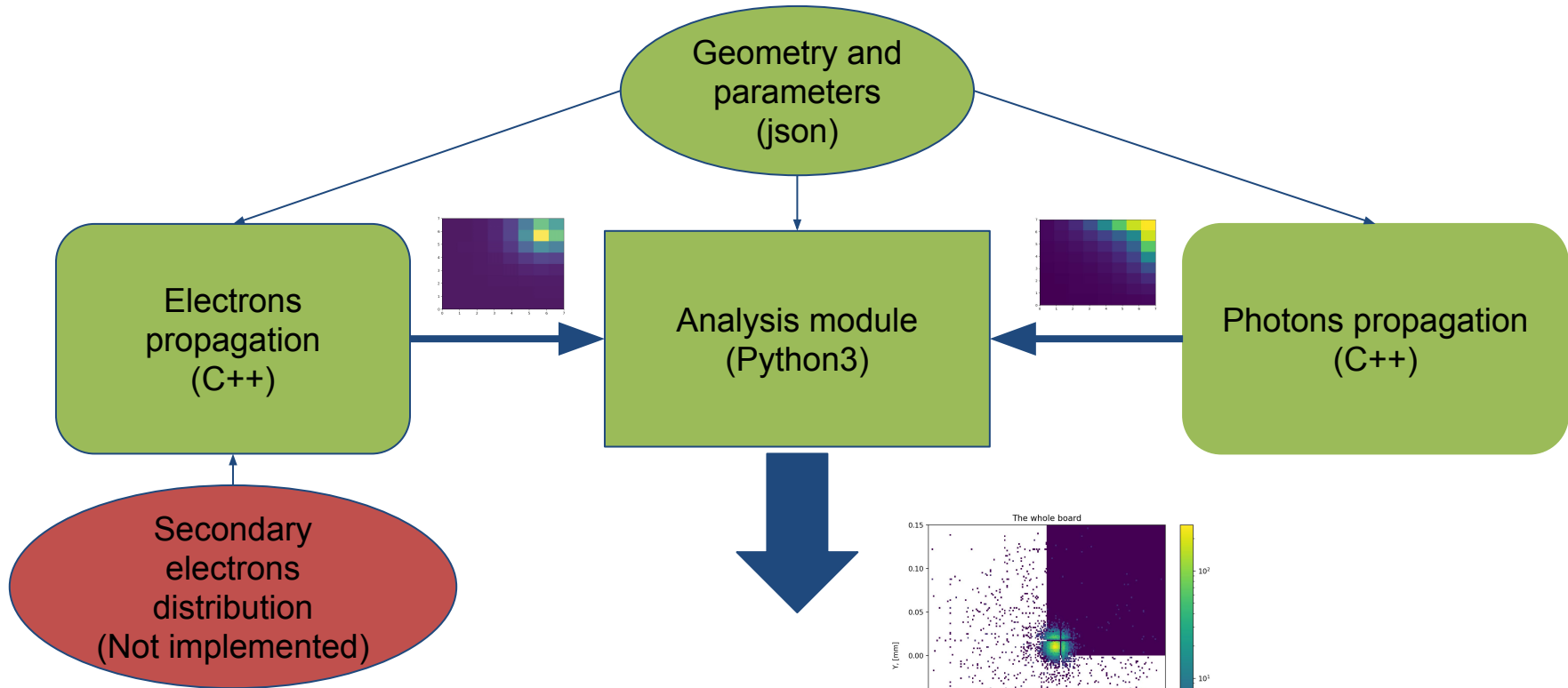
Can trigger another secondary CT



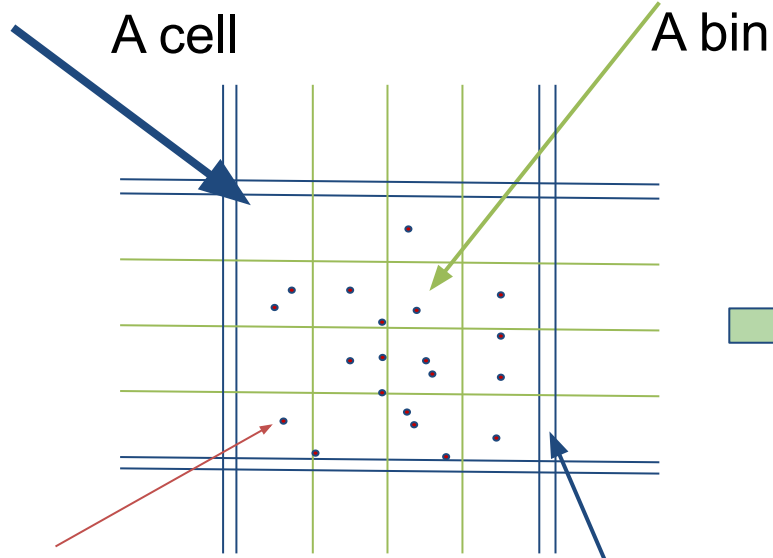
Takes into account secondary CT; ignores 3 order and higher



# Current status of code



# Photons map

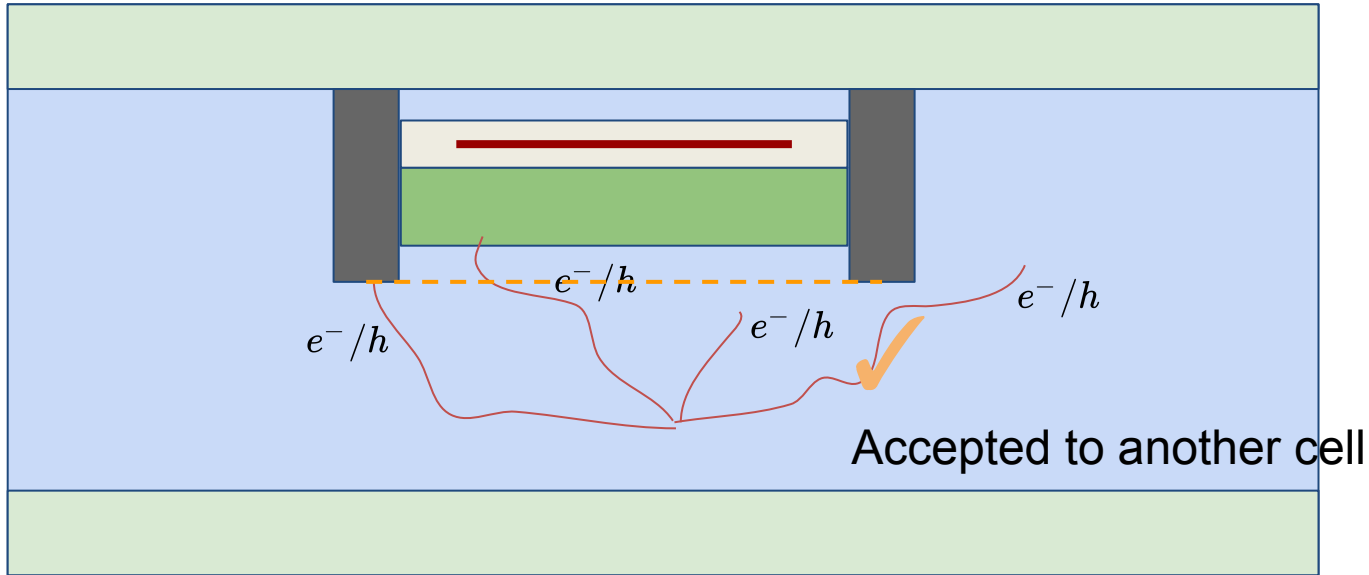


Fraction of photons that belongs to the bin

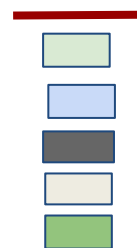
1%	2%	2%	0%
3%	13%	10%	4%
6%	14%	9%	3%
2%	8%	7%	2%

$\Sigma \neq 100\%$  Some photons hit trenches or do not trigger an avalanche

# Electron propagation



--- - electron acceptance Line

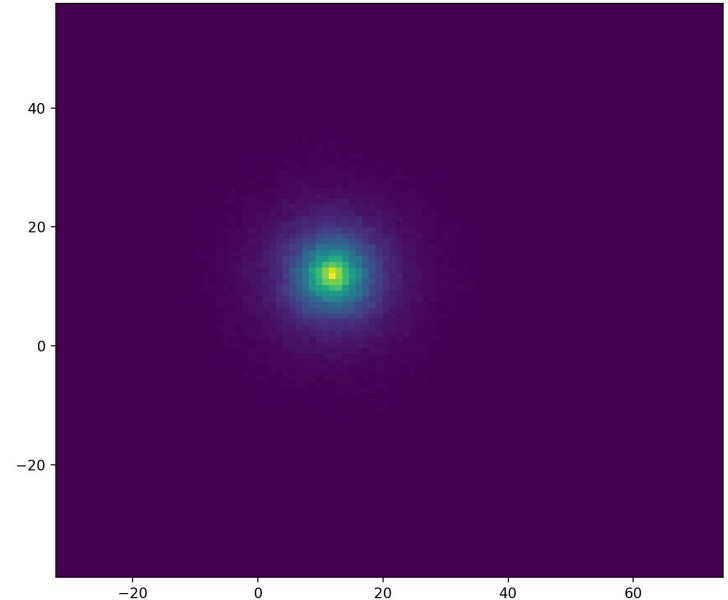


- Initial photons position
- SiO2 layer
- Silicon
- Trenches
- Electron generating region
- Holes generating region

# Example with HPK

100k electrons were injected at a random point in left top corner of central cell. The distance from trenches was set to  $7\mu\text{m}$ .

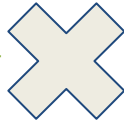
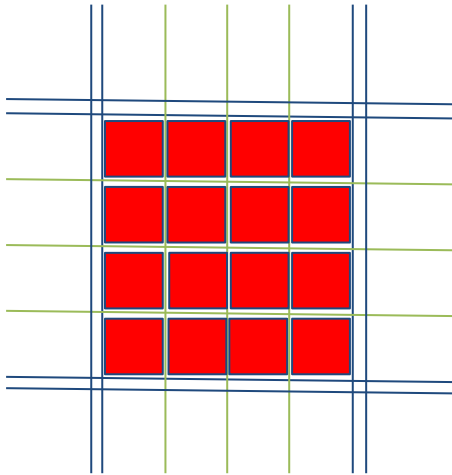
Resulting distribution of the electrons that reached active region.



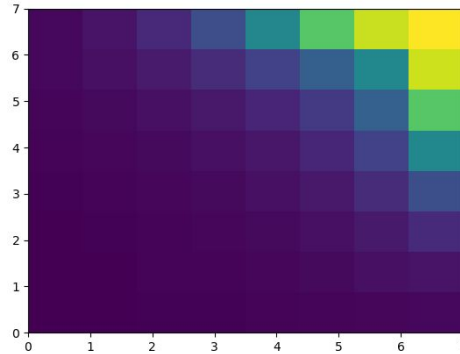
# Analysis: building image

Weightening of injection map with the probabilities given by CT map

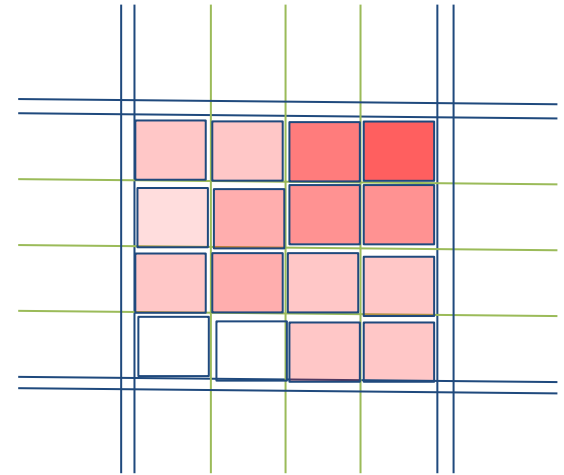
Binned photons  
injection map



Cross Talk map



Resulting combined  
CT data





# Changes in geometry and simulation

HPK trenches are made of tungsten.  
1 million photons in a wavelength range of 440-1000nm were created in the simulation for each geometry.

In new configurations the wavelength range was changed to 660-1200nm and absorption length was taken for doped silicon.

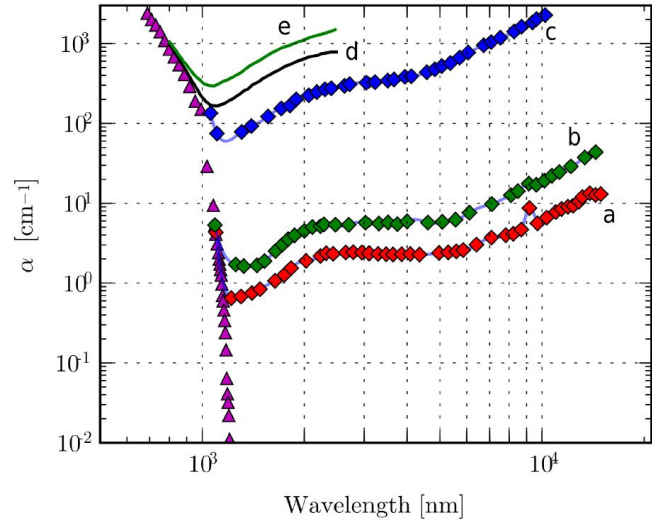
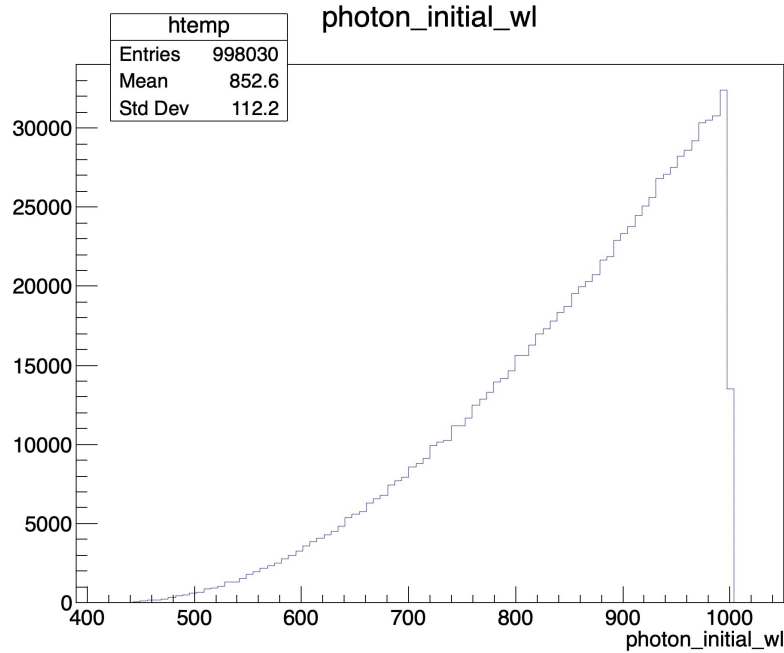


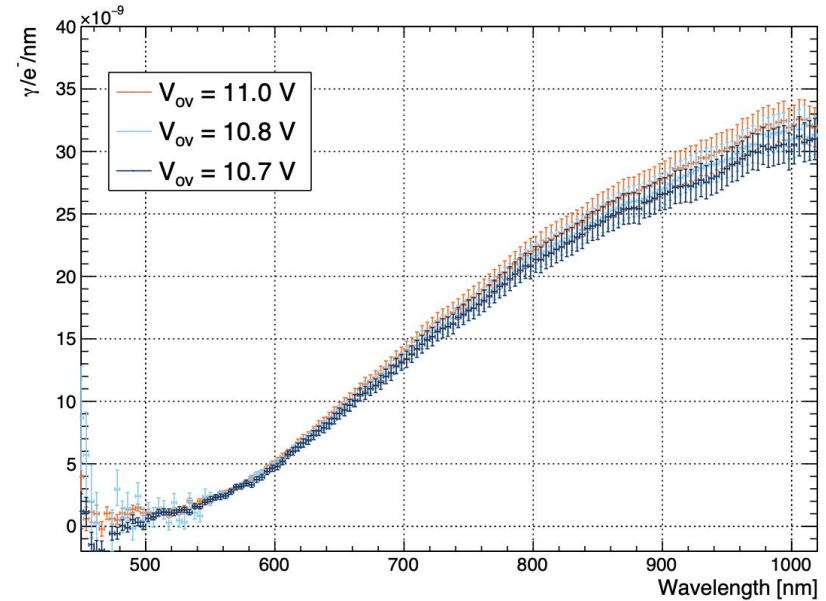
Figure: Absorption coefficient of silicon with different doping

# Emission spectra HPK

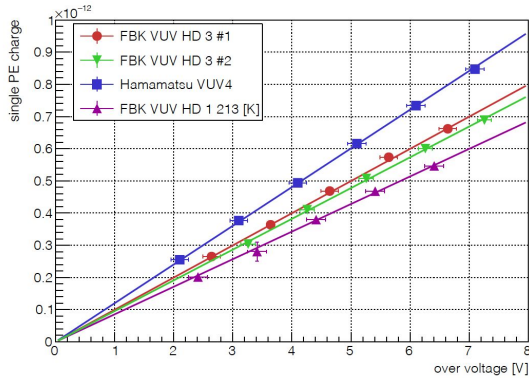
Used in Geant4



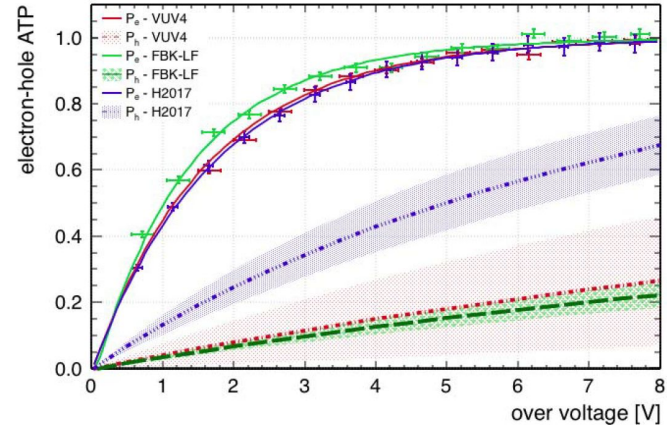
Measured



# Analysis (gain and avalanche probability plots)



**Figure 4.7:** Measured single PE charge as a function of the over voltage for several devices tested for the nEXO experiment. The measurements of the FBK VUV HD 3 and Hamamatsu VUV4 were done at 163 K, while the one of the FBK VUV HD 1 was extrapolated from [59] and reported for a temperature of 213 K.



**Fig. 6.** Electron and hole Avalanche Triggering Probability (ATP),  $P_e(d_p)$  and  $P_h(d_W)$ , for the three SiPMs analyzed in this article. For each  $P_e(d_p)$  are also reported the data of Figs. 3 and 5 used to obtain the corresponding curve. Each  $P_h(d_W)$  is derived using (12). The dashed regions represent the uncertainty on the hole probabilities  $P_h(d_W)$  due to the uncertainty on the effective  $k$  values of Table I.